FAIRCHILD
SEMICONDUCTロR®

## ZTX749

## PNP Low Saturation Transistor

- This device are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.


Absolute Maximum Ratings $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
| :--- | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CEO}}$ | Collector-Emitter Voltage | -25 | V |
| $\mathrm{~V}_{\mathrm{CBO}}$ | Collector-Base Voltage | -35 | V |
| $\mathrm{~V}_{\text {EBO }}$ | Emitter-Base Voltage | -5 | V |
| $\mathrm{I}_{\mathrm{C}}$ | Collector Current $\quad$ - Continuous | -2 | A |
| $\mathrm{~T}_{\mathrm{J}}, \mathrm{T}_{\text {STG }}$ | Operating and Storage Junction Temperature Range | $-55 \sim+150$ | ${ }^{\circ} \mathrm{C}$ |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## NOTES:

1. These ratings are based on a maximum junction temperature of $150^{\circ} \mathrm{C}$
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Off Characteristics |  |  |  |  |  |
| $\mathrm{BV}_{\text {CEO }}$ | Collector-Emitter Breakdown Voltage | $\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}$ | -25 |  | V |
| $\mathrm{BV}_{\text {CBO }}$ | Collector-Base Breakdown Voltage | $\mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A}$ | -35 |  | V |
| $\mathrm{BV}_{\text {EBO }}$ | Emitter-Base Breakdown Voltage | $\mathrm{I}_{\mathrm{E}}=-100 \mu \mathrm{~A}$ | -5 |  | V |
| $\mathrm{I}_{\text {CBO }}$ | Collector Cutoff Current | $\begin{aligned} & \mathrm{V}_{C B}=-30 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CB}}=-30 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C} \end{aligned}$ |  | $\begin{gathered} \hline-100 \\ -10 \\ \hline \end{gathered}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \\ & \hline \end{aligned}$ |
| $\mathrm{I}_{\text {EBO }}$ | Emitter Cutoff Current | $\mathrm{V}_{\mathrm{EB}}=-4 \mathrm{~V}$ |  | -100 | nA |
| On Characteristics* |  |  |  |  |  |
| $\mathrm{h}_{\text {FE }}$ | DC Current Gain | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-50 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-2 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-6 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V} \end{aligned}$ | $\begin{gathered} \hline 70 \\ 100 \\ 75 \\ 15 \\ \hline \end{gathered}$ | 300 |  |
| $\mathrm{V}_{\text {CE }}$ (sat) | Collector-Emitter Saturation Voltage | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-100 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{C}}=-2 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-200 \mathrm{~mA} \end{aligned}$ |  | $\begin{array}{r} \hline-300 \\ -500 \\ \hline \end{array}$ | mV |
| $\mathrm{V}_{\mathrm{BE}}$ (sat) | Base-Emitter Saturation Voltage | $\mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-100 \mathrm{~mA}$ |  | -1.25 | V |
| $\mathrm{V}_{\text {BE }}$ (on) | Base-Emitter On Voltage | $\mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V}$ |  | -1 | V |
| Small-Signal Characteristics |  |  |  |  |  |
| $\mathrm{C}_{\text {obo }}$ | Output Capacitance | $\mathrm{V}_{C B}=-10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1 \mathrm{MHz}$ |  | 100 | PF |
| $\mathrm{f}_{\mathrm{T}}$ | Transition Frequency | $\begin{aligned} & I_{\mathrm{C}}=1-00 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-5 \mathrm{~V} \\ & \mathrm{f}=100 \mathrm{MHz} \end{aligned}$ | 100 |  |  |

Thermal Characteristics $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter | Max. | Units |
| :--- | :--- | :---: | :---: |
| $\mathrm{P}_{\mathrm{D}}$ | Total Device Dissipation | 1 | W |
| $\mathrm{R}_{\text {өJA }}$ | Thermal Resistance, Junction to Ambient | 125 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Package Dimensions

TO-226


$$
\begin{aligned}
& \begin{array}{|l|l|l|}
\hline \overline{\mathrm{Z}} & 99 & 95 \\
\hline 1 & \mathrm{E} & \mathrm{E} \\
\hline 2 & \mathrm{~B} & \mathrm{C} \\
\hline 3 & \mathrm{C} & \mathrm{~B} \\
\hline
\end{array} \\
& \text { TO-226AE }(95,99)
\end{aligned}
$$

For leadformed option ordering, refer to Tape \& Reel data information.

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| :---: | :---: | :---: | :---: | :---: |
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| :--- | :--- | :--- |
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